

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning on page 12, line 19, as follows:

Figs. 11A to ~~[[11G]]~~ 11F are cross-sectional views for each process, depicting cross sections for each main process for explaining an example of a manufacturing method of the electrostatic discharge device of the first embodiment.

Please amend the paragraph beginning on page 31, line 18, as follows:

Figs. 11A to ~~[[11G]]~~ 11F are cross-sectional views for each process, depicting cross sections for each main process for explaining an example of this manufacturing method. Note that these cross-sectional views for each process are depicted by the cross section on arrow along the line A1-A1' in Fig. 9A.

Please amend the paragraph beginning on page 33, line 21, as follows:

Thereafter, by a publicly known method, contact holes are opened in predetermined regions, and a predetermined wiring material selected from aluminum (Al), copper (Cu), alloys, each of which contains either of the above materials as a main material, and the like is deposited therein and patterned (Fig. 11E). If multilayer wiring is required, it is satisfactory that deposition of an interlayer insulating film, the opening of connection holes, and the deposition and patterning of the ~~wiring~~ wiring material are repeated to form the multilayer wiring. Therefore, description thereof will be omitted. Note that contact holes are opened in the p-type diffusion regions 55c and 65c according to needs, which are then coupled (or connected) to a predetermined power supply (usually, the same power supply as a power supply to which the silicon substrate 3 is connected, or a power supply in which VSS is included) by use of the above-described wiring material (Fig. ~~[[11G]]~~ 11F).

AMENDMENTS TO THE DRAWINGS:

Replacement Drawing Sheet 12 is attached hereto and amends the inaccurately labeled "Fig. 11G" so that it is correctly labeled --Fig. 11F--. Applicant respectfully submits that no new matter is added by this amendment.